CORRECTION

[View Article Online](#)
[View Journal](#) | [View Issue](#)

Cite this: *J. Mater. Chem. C*, 2018, **6**, 10376

DOI: 10.1039/c8tc90192a

rsc.li/materials-c

Correction: A selectively processible instant glue passivation layer for indium gallium zinc oxide thin-film transistors fabricated at low temperature

Hyukjoon Yoo, Young Jun Tak, Won-Gi Kim, Yeong-gyu Kim and Hyun Jae Kim*

Correction for 'A selectively processible instant glue passivation layer for indium gallium zinc oxide thin-film transistors fabricated at low temperature' by Hyukjoon Yoo *et al.*, *J. Mater. Chem. C*, 2018, **6**, 6187–6193.

There were errors in the details shown for ref. 2, 6 and 9 cited in this article. The corrected references are shown below as ref. 1–3, respectively.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

References

- 1 J. Sheng, H.-J. Jeong, K.-L. Han, T. Hong and J.-S. Park, *J. Inf. Disp.*, 2017, **18**, 159–172.
- 2 Y. J. Tak, S. P. Park, T. S. Jung, H. Lee, W.-G. Kim, J. W. Park and H. J. Kim, *J. Inf. Disp.*, 2016, **17**, 73–78.
- 3 S. Hong, J. W. Park, H. J. Kim, Y.-G. Kim and H. J. Kim, *J. Inf. Disp.*, 2016, **17**, 93–101.